65 V, 100 mA NPN general-purpose transistors

Rev. 9 — 25 September 2012

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number ^[1]	Package	Package		
	NXP	JEITA	JEDEC	
BC846	SOT23	-	TO-236AB	BC856
BC846W	SOT323	SC-70	-	BC856W
BC846T	SOT416	SC-75	-	BC856T

[1] Valid for all available selection groups.

1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Two different gain selections

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	65	V
I _C	collector current		-	-	100	mA
h _{FE}	DC current gain	V_{CE} = 5 V; I_C = 2 mA	110	-	450	
	h _{FE} group A		110	180	220	
	h _{FE} group B		200	290	450	



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2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
SOT23, S	SOT323, SOT416		
1	base		
2	emitter	3	3
3	collector		1
		1 2 006aaa144	2 sym021

3. Ordering information

Table 4. Order	ring inforn	nation	
Type number ^[1]			
	Name	Description	Version
BC846	-	plastic surface-mounted package; 3 leads	SOT23
BC846W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BC846T	SC-75	plastic surface-mounted package; 3 leads	SOT416

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes Type number Marking code^[1] BC846 1D* 1A* BC846A BC846B 1B* BC846W 1D* BC846AW 1A* BC846BW 1B* BC846T 1M BC846AT 1A BC846BT 1B

[1] * = placeholder for manufacturing site code

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5. Limiting values

Table 6. In accorda	Limiting values nce with the Absolute Maximur	m Rating System (IEC	C 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	80	V
V _{CEO}	collector-emitter voltage	open base	-	65	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	200	mA
I _{BM}	peak base current	single pulse; $t_p \leq 1 ms$	-	200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u>		
	SOT23		-	250	mW
	SOT323		-	200	mW
	SOT416		-	150	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>			
	SOT23		-	-	500	K/W
	SOT323		-	-	625	K/W
	SOT416		-	-	833	K/W
-						

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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7. Characteristics

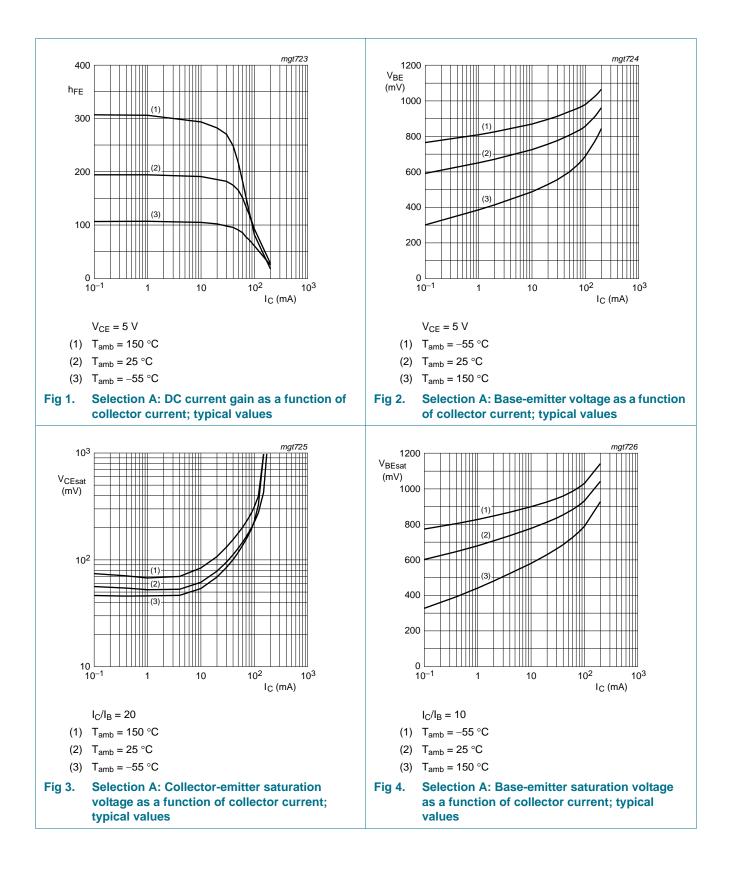
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$		-	-	15	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = 30 \; V; \; I_{E} = 0 \; A; \\ T_{j} = 150 \; ^{\circ}C \end{array}$		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 10 μ A					
	h _{FE} group A			-	180	-	
	h _{FE} group B			-	290	-	
	$\begin{array}{c} h_{FE} \text{ group B} \\ \hline DC \text{ current gain} \\ h_{FE} \text{ group A} \\ \hline h_{FE} \text{ group B} \\ \hline \text{collector-emitter} \\ \text{saturation voltage} \\ \hline base-emitter \\ \text{orduration voltage} \\ \end{array} \begin{array}{c} I_C = 10 \text{ mA; } I_B = 0.5 \text{ m} \\ I_C = 10 \text{ mA; } I_B = 5 \text{ m} \\ I_C = 10 \text{ mA; } I_B = 0.5 \text{ m} \\ \hline I_C = 10 \text{ mA; } I_B = 0.5 \text{ m} \\$	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$		110	-	450	
	h _{FE} group A			110	180	220	
	h _{FE} group B			200	290	450	
V _{CEsat}		I_{C} = 10 mA; I_{B} = 0.5 mA		-	90	200	220 450 200 mV 400 mV - mV
	h _{FE} group B collector-emitter saturation voltage base-emitter	$I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$	<u>[1]</u>	-	200	400	mV
V _{BEsat}		I_{C} = 10 mA; I_{B} = 0.5 mA	[2]	-	760	-	mV
	saturation voltage	$I_{C} = 100 \text{ mA}; I_{B} = 5 \text{ mA}$	[2]	-	900	-	mV
V _{BE}	base-emitter voltage	$I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$	[3]	580	660	700	mV
		I_C = 10 mA; V_{CE} = 5 V	[3]	-	-	770	mV
f _T	transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = 10 \text{ V}; \text{I}_{E} = \text{i}_{e} = 0 \text{ A}; \\ \text{f} = 1 \text{ MHz} \end{array}$		-	2	3	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = i_{c} = 0 \text{ A};$ f = 1 MHz		-	11	-	pF
NF	noise figure	$I_C = 200 \ \mu$ A; V _{CE} = 5 V; R _S = 2 kΩ; f = 1 kHz; B = 200 Hz		-	2	10	dB

[2] V_{BEsat} decreases by approximately 1.7 mV/K with increasing temperature.

[3] V_{BE} decreases by approximately 2 mV/K with increasing temperature.

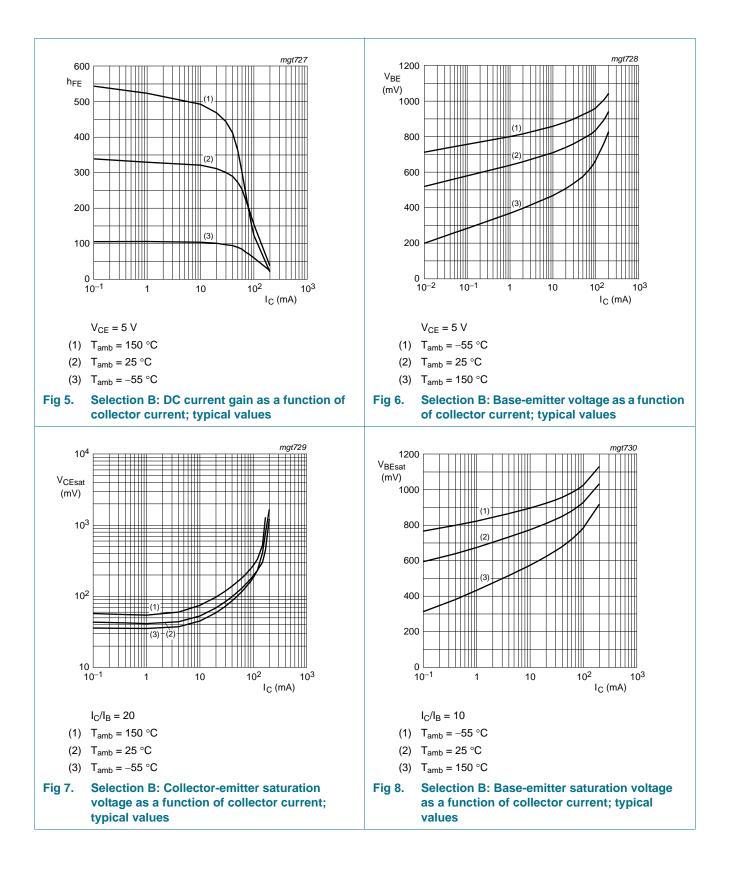
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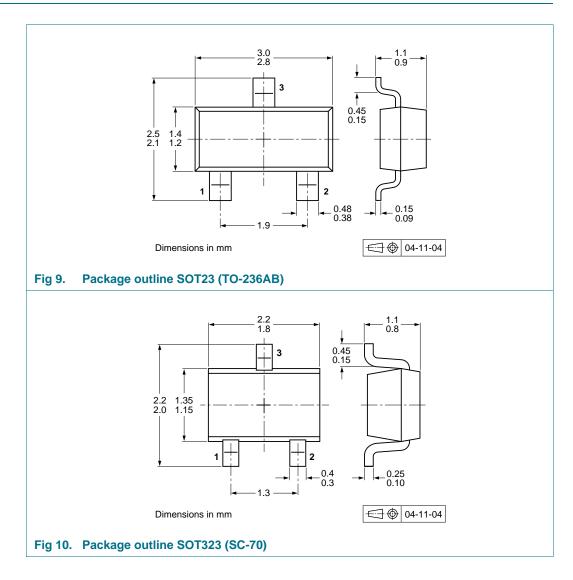
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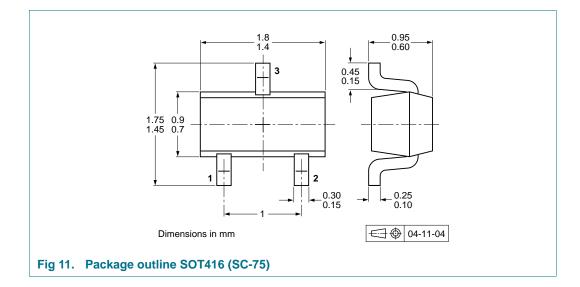
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8. Package outline



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9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

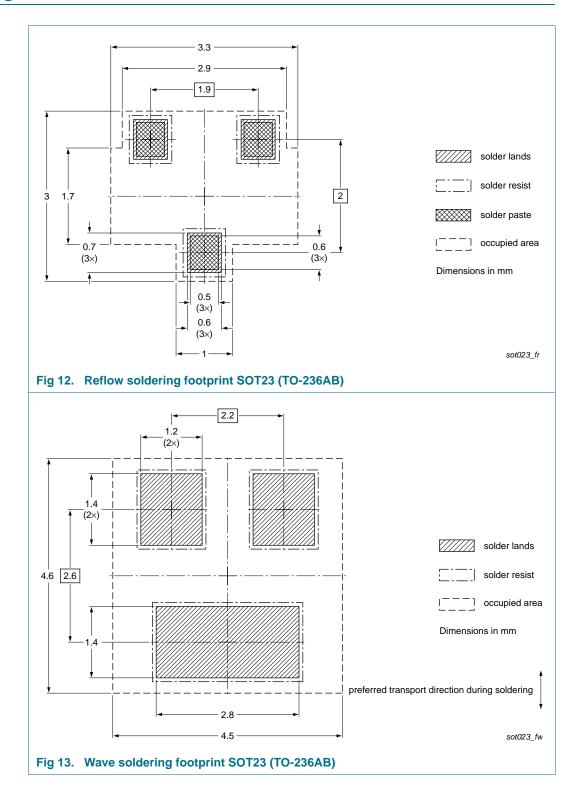
Туре	Package	Description	Packin	ig quant	ity
number ^[2]			1000	3000	4000
BC846	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
BC846W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135
BC846T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

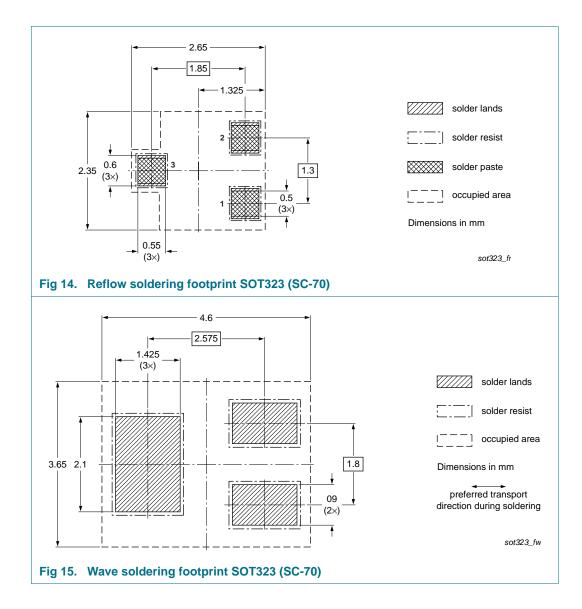
[2] Valid for all available selection groups.

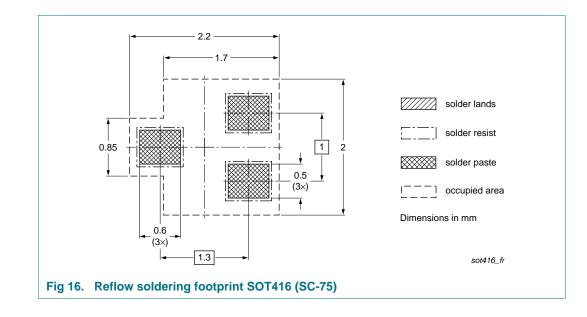
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10. Soldering



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11. Revision history

Document IDRelease dateData sheet statusChange noticeSupersedesBC846_SER v.920120925Product data sheet-BC846_SER v.8Modifications:• Table 6 "Limiting values": Ptot values correctedBC846_BC546_SER v.7BC846_BC546_SER v.720091117Product data sheet-BC846_BC546_SER v.6BC846_BC546_SER v.620060207Product data sheet	Table 10. Revision history				
Modifications: Table 6 "Limiting values": P _{tot} values corrected BC846_SER v.8 20120424 Product data sheet BC846_BC546_SER v.7 BC846_BC546_SER v.7 20091117 Product data sheet PC846_BC546_SER v.6	Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846_SER v.8 20120424 Product data sheet BC846_BC546_SER v.7 BC846_BC546_SER v.7 20091117 Product data sheet - BC846_BC546_SER v.6	BC846_SER v.9	20120925	Product data sheet	-	BC846_SER v.8
BC846_BC546_SER v.7 20091117 Product data sheet - BC846_BC546_SER v.6	Modifications:	• Table 6 "Lir	niting values": P _{tot} values c	orrected	
	BC846_SER v.8	20120424	Product data sheet		BC846_BC546_SER v.7
BC846_BC546_SER v.6 20060207 Product data sheet	BC846_BC546_SER v.7	20091117	Product data sheet	-	BC846_BC546_SER v.6
	BC846_BC546_SER v.6	20060207	Product data sheet	-	-

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Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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